

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,794,709 B2
DATED : September 21, 2004
INVENTOR(S) : Ahn et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, "4,477,310 A", reference, after "Park et al." insert -- 156 --.
"4,700,212 A", reference, after "Okazawa" insert -- 357 --.
"5,057,449 A", reference, after "Lowrey et al." insert -- 438 --.
"5,257,095 A", reference, after "Liu et al." insert -- 257 --.
"5,731,238 A", reference, after "Cavins et al." insert -- 438 --.
"6,091,109 A", reference, after "Hasegawa" insert -- 257 --.
OTHER PUBLICATIONS, "Guo, X., et al.", reference, delete "TiO₂ Si₃N₄" and insert -- TiO₂ Si₃N₄ --, therefor.
After "Han, I.K., et al.", reference, insert -- Hideo, O., et al., "Dual Gate Oxide Process Integration for High Performance Embedded Memory Products", Extended Abstract of the 1998 International Conference on Solid State Devices and Materials, pp. 108-109, (1998) --.
"Togo, M., et al.", reference, delete "DRAMs" and insert -- DRAMs --, therefor.

Column 5.

Line 40, delete "1999International" and insert -- 1999 International --, therefor.

Column 8.

Lines 14 and 15, delete "SiO₂" and insert -- SiO₂ --, therefor.
Lines 30 and 33, delete "source drain" and insert -- source/drain --, therefor.

Column 10.

Lines 28, 32, 45, 60 and 64, delete "SiO₂" and insert -- SiO₂ --, therefor.
Lines 29, 39, 46 and 61, delete "Si₃N₄" and insert -- Si₃N₄ --, therefor.

Column 11.

Lines 21, 25 and 44, delete "SiO₂" and insert -- SiO₂ --, therefor.
Lines 22, 34 and 49, delete "Si₃N₄" and insert -- Si₃N₄ --, therefor.
Line 49, after "nitride" delete "(Si₃N₄)" and insert -- (Si₃N₄) --, therefor.

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Column 12,

Lines 6, 29 and 50, delete "SiO2" and insert -- SiO₂ --, therefor.

Line 35, delete "Si3N4" and insert -- Si₃N₄ --, therefor.

Signed and Sealed this

Tenth Day of May, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office